



CHENMKO ENTERPRISE CO.,LTD

SURFACE MOUNT

High frequency amplifier Transistor

VOLTAGE 6 Volts CURRENT 50 mAmpere

2SC4774PT

Lead free devices

APPLICATION

* Small Signal Amplifier .

FEATURE

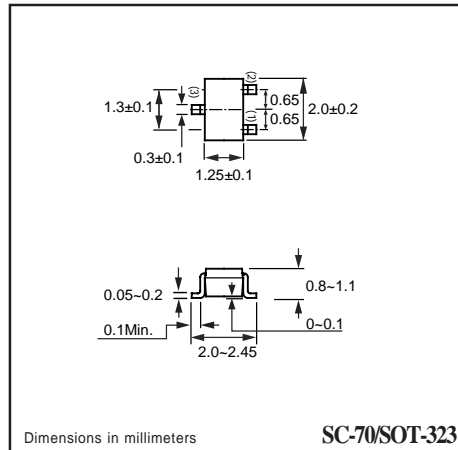
- * Surface mount package. (SC-70/SOT-323)
- * Low saturation voltage $V_{CE(sat)}=0.3V(max.)$
- * Low cob. $C_{ob}=1.0pF(Typ.)$
- * $P_c= 200mW$ (mounted on ceramic substrate).
- * High saturation current capability.

CONSTRUCTION

- * NPN Silicon Transistor
- * Epitaxial planner type

MARKING

* UW



CIRCUIT



MAXIMUM RATINGS (At $T_A = 25^{\circ}C$ unless otherwise noted)

| RATINGS | CONDITION | SYMBOL | MIN. | MAX. | UNITS |
|-------------------------------|---------------------------------|-----------|------|------|-------------|
| Collector - Base Voltage | Open Emitter | V_{cbo} | - | 12 | Volts |
| Collector - Emitter Voltage | Open Base | V_{ceo} | - | 6 | Volts |
| Emitter - Base Voltage | Open Collector | V_{ebo} | - | 3 | Volts |
| Collector Current DC | | I_c | - | 50 | mAmps |
| Total Power Dissipation | $T_A \leq 25^{\circ}C$; Note 1 | P_{TOT} | - | 250 | mW |
| Storage Temperature | | T_{STG} | -55 | +150 | $^{\circ}C$ |
| Junction Temperature | | T_J | - | +150 | $^{\circ}C$ |
| Operating Ambient Temperature | | T_{AMB} | -55 | +150 | $^{\circ}C$ |

Note

1. Transistor mounted on ceramic substrate 50mmX50mmX0.8t.
2. Measured at Pulse Width 300 us, Duty Cycle 2%.

2004-11

RATING CHARACTERISTICS (2SC4774PT)

ELECTRICAL CHARACTERISTICS (At $T_A = 25^\circ\text{C}$ unless otherwise noted)

| PARAMETERS | CONDITION | SYMBOL | MIN. | TYPE | MAX. | UNITS |
|--------------------------------------|--|-------------|------|------|------|---------------|
| Collector Cut-off Current | $I_E=0; V_{CB}=10\text{V}$ | I_{CBO} | - | - | 0.5 | μA |
| Emitter Cut-off Current | $I_C=0; V_{EB}=7\text{V}$ | I_{CEO} | - | - | 0.5 | μA |
| DC Current Gain | $V_{CE}/I_C=5\text{V}/5\text{mA}$ | h_{FE} | 270 | - | 560 | |
| Collector-Emitter Saturation Voltage | $I_C=10\text{mA}; I_B=1\text{mA}$ | V_{CEsat} | - | - | 0.3 | Volts |
| Output-on resistance | $I_B=3\text{mA}; V_I=100\text{mVrms}$ $f=500\text{KHz}$ | R_{on} | - | 2 | - | Ω |
| Output Collector Capacitance | $I_E=I_C=0; V_{CB}=10\text{V};$ $f=1\text{MHz}$ | C_{ob} | - | 1 | 1.7 | pF |
| Transition Frequency | $I_C=10\text{mA}; V_{CE}=5\text{V};$ $f=200\text{MHz}$ | f_T | 300 | 800 | - | MHz |

Note :

1. Pulse test: $t_p \leq 300\mu\text{Sec}$; $\delta \leq 0.02$.

RATING CHARACTERISTIC CURVES (2SC4774PT)

●Electrical characteristic curves

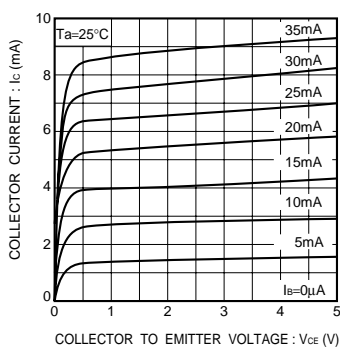


Fig.1 Grounded emitter output characteristics (I)

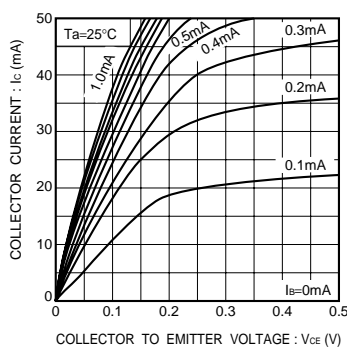


Fig.2 Grounded emitter output characteristics (II)

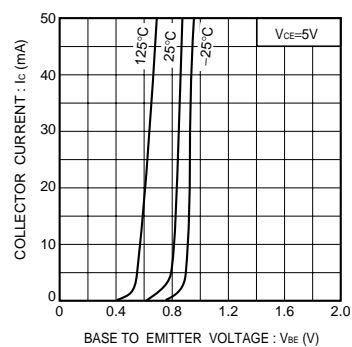


Fig.3 Grounded emitter propagation characteristics

RATING CHARACTERISTIC CURVES (2SC4774PT)

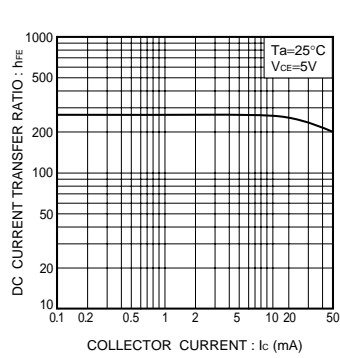


Fig.4 DC current gain vs. collector current

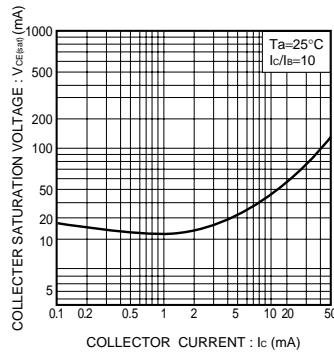


Fig.5 Collector-emitter saturation voltage vs. collector current

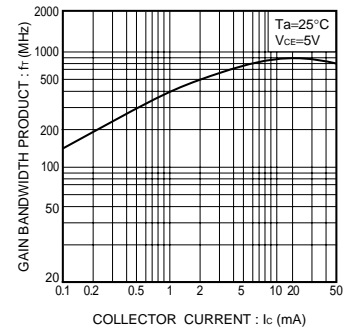


Fig.6 Gain bandwidth product vs. collector current

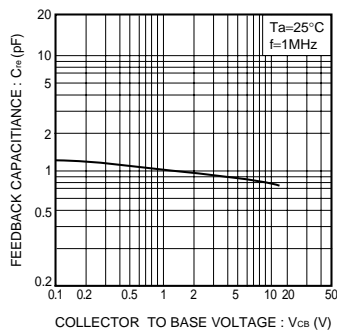


Fig.7 Collector output capacitance vs. voltage

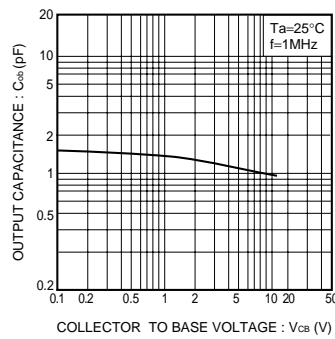


Fig.8 Back capacitance voltage

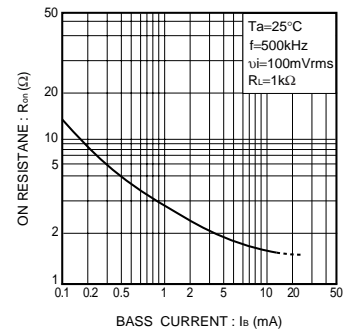


Fig.9 Output-on resistance vs. base current